

IN THE CLAIMS:

Please amend claims 24, 25, 26, and 28 as set forth below. Applicants' note that all claims currently pending in the Application are shown below for clarity.

*Subt F<sup>2</sup>* 23. A gate stack, including a non-crystalline metallic silicide film.

*①* 24. (Twice Amended) A gate stack, including [a crystalline] an amorphous metallic silicide film wherein said metallic silicide film is substantially devoid of silicon clusters.

25. (Twice Amended) A gate stack on a dielectric layered [semiconductor] silicon substrate, comprising:

a polysilicon layer disposed over said dielectric layered [semiconductor] silicon substrate;  
a non-crystalline metallic silicide film disposed over said polysilicon layer; and  
a dielectric cap on said non-crystalline metallic silicide film.

*Subt F<sup>3</sup>* 26. (Amended) A gate stack structure comprising a gate stack on a dielectric layered [semiconductor] silicon substrate wherein [said] a gate dielectric layer of said gate stack is substantially devoid of pitting.

*Subt F<sup>5</sup>* 27. The gate stack structure of claim 26 wherein said a gate stack includes a non-crystalline metallic silicide film.

*③* 28. (Twice Amended) The gate stack structure of claim 26 wherein said [a] gate stack includes [a crystalline] an amorphous metallic silicide film substantially devoid of silicon clusters.